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(54) Title (EN): METHOD OF ETCHING MAGNETORESISTIVE STACK

(54) Title (FR): PROCÉDÉ DE GRAVURE DE PILE MAGNÉTORÉSISTIVE

(57) Abstract:

(EN): Magnetoresistive bit fabrication includes etching through at least a portion of a thickness of a surface region including a hard mask to create a first set of exposed areas in the form of multiple parallel strips extending in a first direction, etching through at least a portion of a thickness of the surface region to create a second set of exposed areas in the form of multiple parallel strips extending in a second direction, preferably transverse to the first direction, and etching through at least a portion of the thickness of the magnetoresistive stack through the first and second sets of exposed areas.

(FR): Selon l'invention, la fabrication de fragments magnétorésistifs consiste à effectuer une gravure à travers au moins une partie d'une épaisseur d'une région de surface comprenant un masque dur pour créer un premier ensemble de zones exposées sous forme de multiples bandes parallèles s'étendant dans une première direction, à effectuer une gravure à travers au moins une partie d'une épaisseur de la région de surface pour créer un second ensemble de zones exposées sous forme de multiples bandes parallèles s'étendant dans une seconde direction, de préférence transversale à la première direction, et à effectuer une gravure à travers au moins une partie de l'épaisseur de l'empilement magnétorésistif à travers les premier et second ensembles de zones exposées.

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